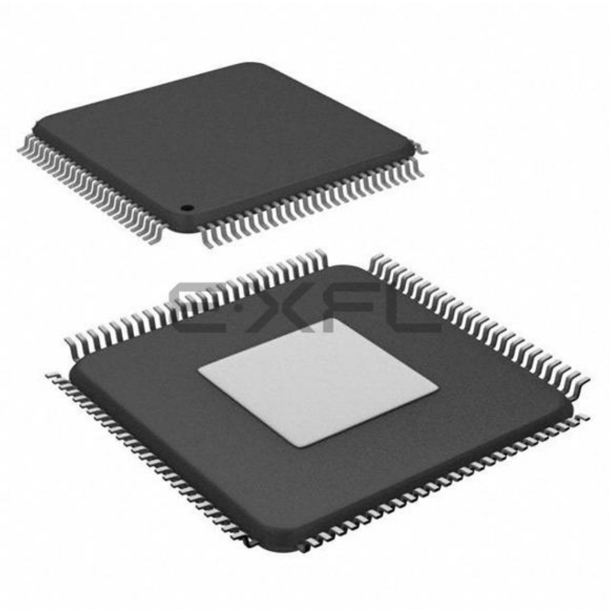

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, UART, USB
Peripherals	DMA, I²S, LED, POR, PWM, WDT
Number of I/O	55
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-11
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4502f100k768acxqma1

Input/Output Lines

- Programmable port driver control module (PORTS)
- Individual bit addressability
- Tri-stated in input mode
- Push/pull or open drain output mode
- Boundary scan test support over JTAG interface

On-Chip Debug Support

- Full support for debug features: 8 breakpoints, CoreSight, trace
- Various interfaces: ARM-JTAG, SWD, single wire trace

1.1 Ordering Information

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. The code “XMC4<DDD>-<Z><PPP><T><FFFF>” identifies:

- <DDD> the derivatives function set
- <Z> the package variant
  - E: LFBGA
  - F: LQFP
  - Q: VQFN
- <PPP> package pin count
- <T> the temperature range:
  - F: -40°C to 85°C
  - X: -40°C to 105°C
  - K: -40°C to 125°C
- <FFFF> the Flash memory size.

For ordering codes for the XMC4500 please contact your sales representative or local distributor.

This document describes several derivatives of the XMC4500 series, some descriptions may not apply to a specific product.

For simplicity the term **XMC4500** is used for all derivatives throughout this document.

	1	2	3	4	5	6	7	8	9	10	11	12	
A	VSS	VDDC	P0.2	P0.3	P0.5	P0.6	P3.6	P0.8	P4.1	P1.8	VDDP	VSS	A
B	VDDP	P3.1	P3.2	P0.10	P0.4	P3.5	P0.7	P4.0	P1.6	P1.7	P1.9	VDDC	B
C	P3.0	P3.13	P0.1	P0.0	P0.13	P0.15	P4.4	P4.6	P4.7	P1.4	P1.2	P1.3	C
D	USB_DM	P3.12	P3.11	P0.9	P0.12	P3.14	P3.15	P4.5	P1.0	P1.5	P1.11	P1.10	D
E	USB_DP	VBUS	P3.8	P3.7	P0.11	P0.14	P3.4	P4.2	P1.1	P1.14	P1.12	P1.13	E
F	RTC_XTAL2	RTC_XTAL1	HIB_IO_1	HIB_IO_0	P3.9	P3.10	P3.3	P4.3	P6.1	P6.4	P6.5	P6.6	F
G	VBAT	P15.3	P15.5	P15.4	P15.6	P15.7	TMS	TCK	P6.3	P6.0	$\overline{\text{PORST}}$	P1.15	G
H	P15.2	P14.15	P14.14	P14.13	P5.10	P5.8	P5.2	P5.1	P5.0	P6.2	XTAL1	XTAL2	H
J	P14.12	P14.7	P14.6	P14.3	P5.11	P2.15	P5.7	P5.5	P2.6	P5.3	P2.0	VSSO	J
K	P14.4	P14.5	P14.2	P15.15	P15.12	P5.9	P2.14	P5.6	P2.7	P5.4	P2.2	P2.1	K
L	VDDA	P14.1	P14.0	P15.14	P14.9	P15.9	P2.12	P2.10	P2.8	P2.4	P2.3	VDDP	L
M	VSSA	VAGND	VAREF	P15.13	P14.8	P15.8	P2.13	P2.11	P2.9	P2.5	VDDC	VSS	M
	1	2	3	4	5	6	7	8	9	10	11	12	

XMC4500- (top view)

Figure 6 XMC4500 PG-LFBGA-144 Pin Configuration (top view)

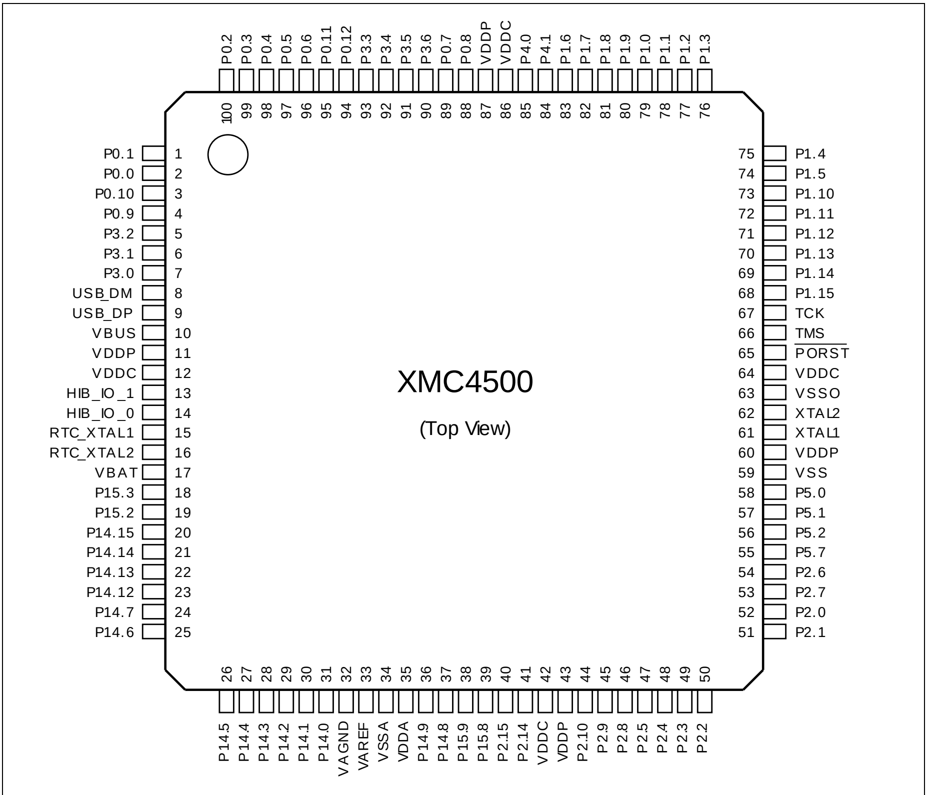

Figure 7 XMC4500 PG-LQFP-100 Pin Configuration (top view)

2.2.2.1 Port I/O Function Table

Table 11 Port I/O Functions

Function	Outputs						Inputs										
	ALT1	ALT2	ALT3	ALT4	HWO0	HWO1	HWI0	HWI1	Input	Input	Input	Input	Input	Input	Input	Input
P0.0		CAN. N0_TXD	CCU80. OUT21	LEDTS0. COL2					U1C1. DX0D	ETH0. CLK_RMIIB	ERU0. 0B0					ETH0. CLKRXB
P0.1	USB. DRIVEVBUS	U1C1. DOUT0	CCU80. OUT11	LEDTS0. COL3						ETH0. CRS_DVB	ERU0. 0A0					ETH0. RXDVB
P0.2		U1C1. SELO1	CCU80. OUT01		U1C0. DOUT3	EBU. AD0	U1C0. HWIN3	EBU. D0	ETH0. RXD0B		ERU0. 3B3					
P0.3			CCU80. OUT20		U1C0. DOUT2	EBU. AD1	U1C0. HWIN2	EBU. D1	ETH0. RXD1B			ERU1. 3B0				
P0.4	ETH0. TX_EN		CCU80. OUT10		U1C0. DOUT1	EBU. AD2	U1C0. HWIN1	EBU. D2		U1C0. DX0A	ERU0. 2B3					
P0.5	ETH0. TXD0	U1C0. DOUT0	CCU80. OUT00		U1C0. DOUT0	EBU. AD3	U1C0. HWIN0	EBU. D3		U1C0. DX0B		ERU1. 3A0				
P0.6	ETH0. TXD1	U1C0. SELO0	CCU80. OUT30			EBU. $\overline{ADV}$				U1C0. DX2A	ERU0. 3B2		CCU80. IN2B			
P0.7	WWDT. SERVICE_OUT	U0C0. SELO0				EBU. AD6	DB. TDI	EBU. D6	U0C0. DX2B	DSD. DIN1A	ERU0. 2B1		CCU80. IN0A	CCU80. IN1A	CCU80. IN2A	CCU80. IN3A
P0.8	SCU. EXTCLK	U0C0. SCLKOUT				EBU. AD7	DB. $\overline{TRST}$	EBU. D7	U0C0. DX1B	DSD. DIN0A	ERU0. 2A1		CCU80. IN1B			
P0.9		U1C1. SELO0	CCU80. OUT12	LEDTS0. COL0	ETH0. MDO	EBU. $\overline{CS1}$	ETH0. MDIA		U1C1. DX2A	USB. ID	ERU0. 1B0					
P0.10	ETH0. MDC	U1C1. SCLKOUT	CCU80. OUT02	LEDTS0. COL1					U1C1. DX1A		ERU0. 1A0					
P0.11		U1C0. SCLKOUT	CCU80. OUT31		SDMMC. $\overline{RST}$	EBU. $\overline{BREQ}$			ETH0. RXERB	U1C0. DX1A	ERU0. 3A2					
P0.12		U1C1. SELO0	CCU40. OUT3			EBU. $\overline{HLDA}$		EBU. $\overline{HLDA}$		U1C1. DX2B	ERU0. 2B2					
P0.13		U1C1. SCLKOUT	CCU40. OUT2							U1C1. DX1B	ERU0. 2A2					
P0.14		U1C0. SELO1	CCU40. OUT1		U1C1. DOUT3		U1C1. HWIN3						CCU42. IN3C			
P0.15		U1C0. SELO2	CCU40. OUT0		U1C1. DOUT2		U1C1. HWIN2						CCU42. IN2C			
P1.0	DSD. CGPWMN	U0C0. SELO0	CCU40. OUT3	ERU1. PDOUT3					U0C0. DX2A		ERU0. 3B0		CCU40. IN3A			
P1.1	DSD. CGPWMP	U0C0. SCLKOUT	CCU40. OUT2	ERU1. PDOUT2			SDMMC. SDWC		U0C0. DX1A	POSIF0. IN2A	ERU0. 3A0		CCU40. IN2A			
P1.2			CCU40. OUT1	ERU1. PDOUT1	U0C0. DOUT3	EBU. AD14	U0C0. HWIN3	EBU. D14		POSIF0. IN1A		ERU1. 2B0	CCU40. IN1A			
P1.3		U0C0. MCLKOUT	CCU40. OUT0	ERU1. PDOUT0	U0C0. DOUT2	EBU. AD15	U0C0. HWIN2	EBU. D15		POSIF0. IN0A		ERU1. 2A0	CCU40. IN0A			
P1.4	WWDT. SERVICE_OUT	CAN. N0_TXD	CCU80. OUT33	CCU81. OUT20	U0C0. DOUT1		U0C0. HWIN1		U0C0. DX0B	CAN. N1_RXDD	ERU0. 2B0		CCU41. IN0C			

Table 11 Port I/O Functions (cont'd)

Function	Outputs						Inputs									
	ALT1	ALT2	ALT3	ALT4	HWO0	HWO1	HWI0	HWI1	Input	Input	Input	Input	Input	Input	Input	Input
P15.12												VADC. G3CH4				
P15.13												VADC. G3CH5				
P15.14												VADC. G3CH6				
P15.15												VADC. G3CH7				
USB_DP																
USB_DM																
HIB_IO_0	HIBOUT	WWDT. SERVICE_OUT							WAKEUPA							
HIB_IO_1	HIBOUT	WWDT. SERVICE_OUT							WAKEUPB							
TCK							DB.TCK/ SWCLK									
TMS					DB.TMS/ SWDIO											
$\overline{\text{PORST}}$																
XTAL1									U0C0. DX0F	U0C1. DX0F	U1C0. DX0F	U1C1. DX0F	U2C0. DX0F	U2C1. DX0F		
XTAL2																
RTC_XTAL1											ERU0. 1B1					
RTC_XTAL2																

Table 22 Standard Pads Class_A2

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.		Max.		
Input Leakage current	I_{OZA2} CC	-6		6	µA	0 V ≤ V_{IN} < 0.5*V_{DDP} - 1 V; 0.5*V_{DDP} + 1 V <V_{IN} ≤ V_{DDP}
		-3		3	µA	0.5*V_{DDP} - 1 V < V_{IN} < 0.5*V_{DDP} + 1 V
Input high voltage	V_{IHA2} SR	0.6 × V_{DDP}		V_{DDP} + 0.3	V	max. 3.6 V
Input low voltage	V_{ILA2} SR	-0.3		0.36 × V_{DDP}	V	
Output high voltage, POD = weak	V_{OHA2} CC	V_{DDP} - 0.4		–	V	I_{OH} ≥ -400 µA
		2.4		–	V	I_{OH} ≥ -500 µA
Output high voltage, POD = medium		V_{DDP} - 0.4		–	V	I_{OH} ≥ -1.4 mA
		2.4		–	V	I_{OH} ≥ -2 mA
Output high voltage, POD = strong		V_{DDP} - 0.4		–	V	I_{OH} ≥ -1.4 mA
		2.4		–	V	I_{OH} ≥ -2 mA
Output low voltage, POD = weak	V_{OLA2} CC	–		0.4	V	I_{OL} ≤ 500 µA
Output low voltage, POD = medium		–		0.4	V	I_{OL} ≤ 2 mA
Output low voltage, POD = strong		–		0.4	V	I_{OL} ≤ 2 mA

3.2.2 Analog to Digital Converters (VADC)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 23 VADC Parameters (Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Analog reference voltage[5]	V_{AREF} SR	V_{AGND} + 1	–	V_{DDA} + 0.05[1]	V	
Analog reference ground[5]	V_{AGND} SR	V_{SSM} - 0.05	–	V_{AREF} - 1	V	
Analog reference voltage range[2)5]	V_{AREF} - V_{AGND} SR	1	–	V_{DDA} + 0.1	V	
Analog input voltage	V_{AIN} SR	V_{AGND}	–	V_{DDA}	V	
Input leakage at analog inputs[3]	I_{OZ1} CC	-100	–	200	nA	$0.03 \times V_{DDA} < V_{AIN} < 0.97 \times V_{DDA}$
		-500	–	100	nA	$0\ \text{V} \leq V_{AIN} \leq 0.03 \times V_{DDA}$
		-100	–	500	nA	$0.97 \times V_{DDA} \leq V_{AIN} \leq V_{DDA}$
Input leakage current at VAREF	I_{OZ2} CC	-1	–	1	µA	$0\ \text{V} \leq V_{AREF} \leq V_{DDA}$
Input leakage current at VAGND	I_{OZ3} CC	-1	–	1	µA	$0\ \text{V} \leq V_{AGND} \leq V_{DDA}$
Internal ADC clock	f_{ADCI} CC	2	–	30	MHz	V_{DDA} = 3.3 V
Switched capacitance at the analog voltage inputs[4]	C_{AINSW} CC	–	7	20	pF	
Total capacitance of an analog input	C_{AINTOT} CC	–	25	30	pF	
Switched capacitance at the positive reference voltage input[5)6]	C_{AREFSW} CC	–	15	30	pF	
Total capacitance of the voltage reference inputs[5]	$C_{AREFTOT}$ CC	–	20	40	pF	

Table 23 VADC Parameters (Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Total Unadjusted Error	TUE CC	-4	–	4	LSB	12-bit resolution; V_{DDA} = 3.3 V; $V_{AREF} = V_{DDA}$ 7)
Differential Non-Linearity Error 8)	EA_{DNL} CC	-3	–	3	LSB	
Gain Error 8)	EA_{GAIN} CC	-4	–	4	LSB	
Integral Non-Linearity 8)	EA_{INL} CC	-3	–	3	LSB	
Offset Error 8)	EA_{OFF} CC	-4	–	4	LSB	
Worst case ADC V_{DDA} power supply current per active converter	I_{DDAA} CC	–	1.5	2	mA	during conversion V_{DDP} = 3.6 V, T_J = 150 °C
Charge consumption on V_{AREF} per conversion 5)	Q_{CONV} CC	–	30	–	pC	0 V ≤ V_{AREF} ≤ V_{DDA} 9)
ON resistance of the analog input path	R_{AIN} CC	–	700	1 700	Ohm	
ON resistance for the ADC test (pull down for AIN7)	R_{AIN7T} CC	180	550	900	Ohm	
Resistance of the reference voltage input path	R_{AREF} CC	–	700	1 700	Ohm	

1) A running conversion may become imprecise in case the normal conditions are violated (voltage overshoot).

2) If the analog reference voltage is below V_{DDA}, then the ADC converter errors increase. If the reference voltage is reduced by the factor k (k<1), TUE, DNL, INL, Gain, and Offset errors increase also by the factor 1/k.

3) The leakage current definition is a continuous function, as shown in figure ADCx Analog Inputs Leakage. The numerical values defined determine the characteristic points of the given continuous linear approximation - they do not define step function (see **Figure 16**).

4) The sampling capacity of the conversion C-network is pre-charged to $V_{AREF}/2$ before the sampling moment. Because of the parasitic elements, the voltage measured at AINx can deviate from $V_{AREF}/2$.

5) Applies to AINx, when used as alternate reference input.

6) This represents an equivalent switched capacitance. This capacitance is not switched to the reference voltage at once. Instead, smaller capacitances are successively switched to the reference voltage.

7) For 10-bit conversions, the errors are reduced to 1/4; for 8-bit conversions, the errors are reduced to 1/16. Never less than ±1 LSB.

8) The sum of DNL/INL/GAIN/OFF errors does not exceed the related total unadjusted error TUE.

9) The resulting current for a conversion can be calculated with $I_{AREF} = Q_{CONV} / t_c$.
The fastest 12-bit post-calibrated conversion of t_c = 550 ns results in a typical average current of I_{AREF} = 54.5 µA.

3.2.3 Digital to Analog Converters (DAC)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 25 DAC Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
RMS supply current	I_{DD}	CC	–	2.5	4	mA	per active DAC channel, without load currents of DAC outputs
Resolution	RES	CC	–	12	–	Bit	
Update rate	f_{URATE_A}	CC	–		2	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 1LSB accuracy
Update rate	f_{URATE_F}	CC	–		5	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 4 LSB accuracy
Settling time	t_{SETTLE}	CC	–	1	2	µs	at full scale jump, output voltage reaches target value ± 20 LSB
Slew rate	SR	CC	2	5	–	V/µs	
Minimum output voltage	V_{OUT_MIN}	CC	–	0.3	–	V	code value unsigned: 000_H; signed: 800_H
Maximum output voltage	V_{OUT_MAX}	CC	–	2.5	–	V	code value unsigned: FFF_H; signed: $7FF_H$
Integral non-linearity	INL	CC	-4	±2.5	4	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF
Differential non-linearity	DNL	CC	-2	±1	2	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF

Table 25 DAC Parameters (Operating Conditions apply) (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Offset error	ED_{OFF} CC		±20		mV	
Gain error	ED_{G_IN} CC	-6.5	-1.5	3	%	
Startup time	$t_{STARTUP}$ CC	–	15	30	µs	time from output enabling till code valid ±16 LSB
3dB Bandwidth of Output Buffer	f_{C1} CC	2.5	5	–	MHz	verified by design
Output sourcing current	I_{OUT_SOURCE} CC	–	-30	–	mA	
Output sinking current	I_{OUT_SINK} CC	–	0.6	–	mA	
Output resistance	R_{OUT} CC	–	50	–	Ohm	
Load resistance	R_L SR	5	–	–	kOhm	
Load capacitance	C_L SR	–	–	50	pF	
Signal-to-Noise Ratio	*SNR* CC	–	70	–	dB	examination bandwidth < 25 kHz
Total Harmonic Distortion	*THD* CC	–	70	–	dB	examination bandwidth < 25 kHz
Power Supply Rejection Ratio	*PSRR* CC	–	56	–	dB	to V_{DDA} verified by design

Conversion Calculation

Unsigned:
DACxDATA = 4095 × $(V_{OUT} - V_{OUT\_MIN}) / (V_{OUT\_MAX} - V_{OUT\_MIN})$

Signed:
DACxDATA = 4095 × $(V_{OUT} - V_{OUT\_MIN}) / (V_{OUT\_MAX} - V_{OUT\_MIN}) - 2048$

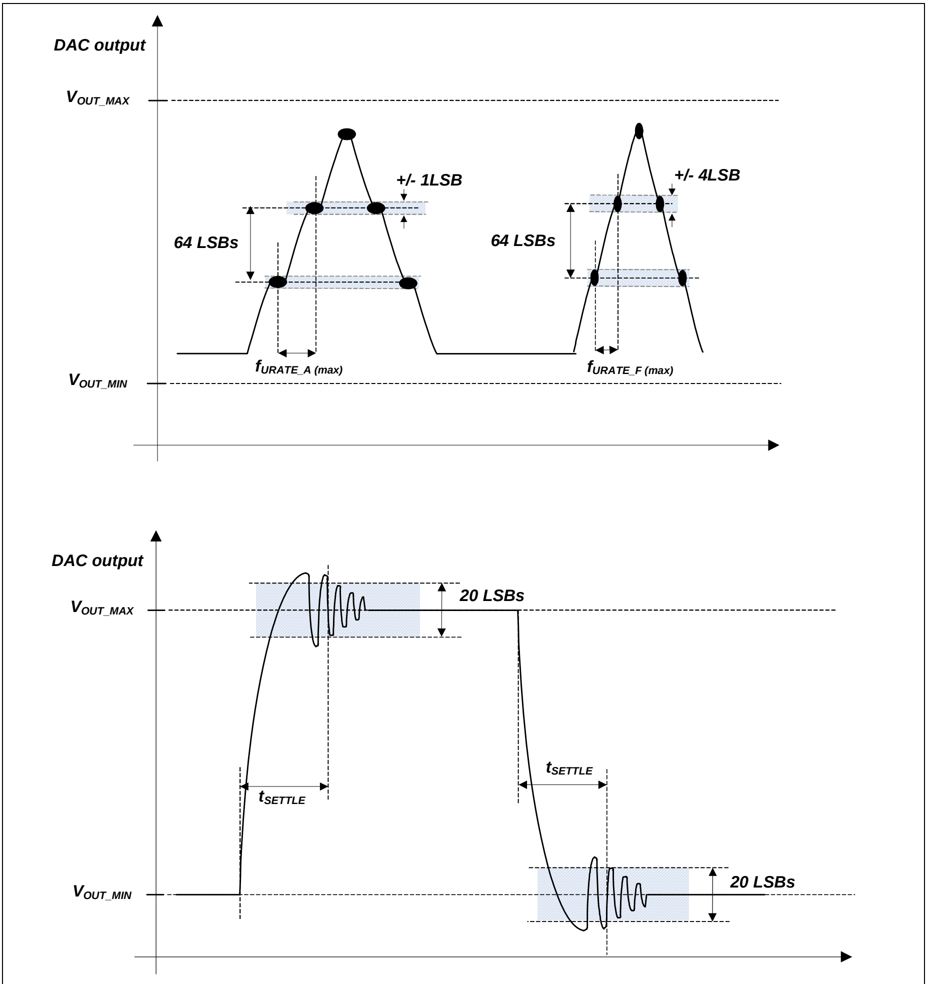

Figure 17 DAC Conversion Examples

Table 30 OSC_XTAL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input frequency	f_{OSC} SR	4	–	40	MHz	Direct Input Mode selected
		4	–	25	MHz	External Crystal Mode selected
Oscillator start-up time[1)2)]	t_{OSCS} CC	–	–	10	ms	
Input voltage at XTAL1	V_{IX} SR	-0.5	–	V_{DDP} + 0.5	V	
Input amplitude (peak-to-peak) at XTAL1[2)3)]	V_{PPX} SR	0.4 × V_{DDP}	–	V_{DDP} + 1.0	V	
Input high voltage at XTAL1[4)]	V_{IHBX} SR	1.0	–	V_{DDP} + 0.5	V	
Input low voltage at XTAL1[4)]	V_{ILBX} SR	-0.5	–	0.4	V	
Input leakage current at XTAL1	I_{ILX1} CC	-100	–	100	nA	Oscillator power down $0\text{ V} \leq V_{IX} \leq V_{DDP}$

1) t_{OSCS} is defined from the moment the oscillator is enabled wih SCU_OSCHPCTRL.MODE until the oscillations reach an amplitude at XTAL1 of 0.4 * V_{DDP}.

2) The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.

3) If the shaper unit is enabled and not bypassed.

4) If the shaper unit is bypassed, dedicated DC-thresholds have to be met.

3.2.8 Power Supply Current

The total power supply current defined below consists of a leakage and a switching component.

Application relevant values are typically lower than those given in the following tables, and depend on the customer's system operating conditions (e.g. thermal connection or used application configurations).

Note: These parameters are not subject to production test, but verified by design and/or characterization.

If not stated otherwise, the operating conditions for the parameters in the following table are:
V_{DDP} = 3.3 V, T_A = 25 °C

Table 32 Power Supply Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Active supply current[1)10)] Peripherals enabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPA}	CC	–	122	–	mA	120 / 120 / 120
			–	110	–		120 / 60 / 60
			–	85	–		60 / 60 / 120
			–	65	–		24 / 24 / 24
			–	52	–		1 / 1 / 1
Active supply current Code execution from RAM Flash in Sleep mode	I_{DDPA}	CC	–	98	–	mA	120 / 120 / 120
			–	80	–		120 / 60 / 60
Active supply current[2)] Peripherals disabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPA}	CC	–	115	–	mA	120 / 120 / 120
			–	105	–		120 / 60 / 60
			–	80	–		60 / 60 / 120
			–	63	–		24 / 24 / 24
			–	50	–		1 / 1 / 1
Sleep supply current[3)] Peripherals enabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS}	CC	–	115	–	mA	120 / 120 / 120
			–	105	–		120 / 60 / 60
			–	83	–		60 / 60 / 120
			–	60	–		24 / 24 / 24
			–	48	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz			–	46	–		100 / 100 / 100

Table 32 Power Supply Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sleep supply current[4] Peripherals disabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	110	–	mA	120 / 120 / 120
		–	100	–		120 / 60 / 60
		–	77	–		60 / 60 / 120
		–	59	–		24 / 24 / 24
		–	48	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Deep Sleep supply current[5] Flash in Sleep mode Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPD} CC	–	20	–	mA	24 / 24 / 24
		–	12	–		4 / 4 / 4
		–	10	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	6	–		100 / 100 / 100 [6]
Hibernate supply current RTC on[7]	I_{DDPH} CC	–	10	–	µA	V_{BAT} = 3.3 V
		–	7.5	–		V_{BAT} = 2.4 V
		–	6.2	–		V_{BAT} = 2.0 V
Hibernate supply current RTC off[8]	I_{DDPH} CC	–	9.2	–	µA	V_{BAT} = 3.3 V
		–	6.7	–		V_{BAT} = 2.4 V
		–	5.6	–		V_{BAT} = 2.0 V
Worst case active supply current[9]	I_{DDPA} CC	–	–	180 [10]	mA	V_{DDP} = 3.6 V, T_J = 150 °C
V_{DDA} power supply current	I_{DDA} CC	–	–	–[11]	mA	
I_{DDP} current at $\overline{\text{PORST}}$ Low	I_{DDP_PORST} CC	–	–	16	mA	V_{DDP} = 3.6 V, T_J = 150 °C
Power Dissipation	P_{DISS} CC	–	–	1	W	V_{DDP} = 3.6 V, T_J = 150 °C
Wake-up time from Sleep to Active mode	t_{SSA} CC	–	6	–	cycles	

Table 44 USIC SSC Slave Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DX1 slave clock period	t_{CLK}	SR	66.6	–	–	ns	
Select input DX2 setup to first clock input DX1 transmit edge[1]	t_{10}	SR	3	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge[1]	t_{11}	SR	4	–	–	ns	
Receive data input DX0/DX[5:3] setup time to shift clock receive edge[1]	t_{12}	SR	6	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge[1]	t_{13}	SR	4	–	–	ns	
Data output DOUT[3:0] valid time	t_{14}	CC	0	–	24	ns	

1) This input timing is valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).

Full-Speed Read Meeting Hold (Minimum Delay)

The following equations show how to calculate the allowed combined propagation delay range of the SD_CLK and SD_DAT/CMD signals on the PCB.

(6)

$$t_{CLK\_DELAY} + t_{OH} + t_{DATA\_DELAY} + t_{TAP\_DELAY} > t_{IH\_F}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} > t_{IH\_F} - t_{OH} - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} > 2 - t_{TAP\_DELAY}$$

The data + clock delay must be greater than 2 ns if t_{TAP_DELAY} is not used.

If the t_{TAP_DELAY} is programmed to at least 2 ns, the data + clock delay must be greater than 0 ns (or less). This is always fulfilled.

AC Timing Specifications (High-Speed Mode)

Table 51 SDMMC Timing for High-Speed Mode

Parameter	Symbol		Values		Unit	Note/ Test Condition
			Min.	Max.		
Clock frequency in high speed transfer mode ($1/t_{pp}$)	f_{pp}	CC	0	48	MHz	
Clock cycle in high speed transfer mode	t_{pp}	CC	20	–	ns	
Clock low time	t_{WL}	CC	7	–	ns	
Clock high time	t_{WH}	CC	7	–	ns	
Clock rise time	t_{TLH}	CC	–	3	ns	
Clock fall time	t_{THL}	CC	–	3	ns	
Inputs setup to clock rising edge	t_{ISU_H}	SR	2	–	ns	
Inputs hold after clock rising edge	t_{IH_H}	SR	2	–	ns	
Outputs valid time in high speed mode	t_{ODLY_H}	CC	–	14	ns	
Outputs hold time in high speed mode	t_{OH_H}	CC	2	–	ns	

Write Timing

Table 55 Asynchronous Write Timing, Multiplexed and Demultiplexed

Parameter			Symbol	Limit Values		Unit
				Min.	Max.	
A(24:0) output delay	to RD/$\overline{\text{WR}}$ rising edge, deviation from the ideal programmed value.	CC	t_{30}	-2.5	2.5	ns
A(24:0) output delay		CC	t_{31}	-2.5	2.5	
$\overline{\text{CS}}$ rising edge		CC	t_{32}	-2	2	
$\overline{\text{ADV}}$ rising edge		CC	t_{33}	-2	4.5	
$\overline{\text{BC}}$ rising edge		CC	t_{34}	-2.5	2	
$\overline{\text{WAIT}}$ input setup		SR	t_{35}	12	–	
$\overline{\text{WAIT}}$ input hold		SR	t_{36}	0	–	
Data output delay		CC	t_{37}	-5.5	2	
Data output delay		CC	t_{38}	-5.5	2	
RD / $\overline{\text{WR}}$ output delay		CC	t_{39}	-2.5	1.5	

3.3.10.2 EBU Burst Mode Access Timing

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Note: Operating Conditions apply, with Class A2 pins and C_L = 16 pF.

Table 56 EBU Burst Mode Read / Write Access Timing Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Output delay from BFCLKO rising edge	t_{10}	CC	-2	–	2	ns	–
$\overline{\text{RD}}$ and RD/$\overline{\text{WR}}$ active/inactive after BFCLKO active edge[1)]	t_{12}	CC	-2	–	2	ns	–
$\overline{\text{CS}}$x output delay from BFCLKO active edge[1)]	t_{21}	CC	-2.5	–	1.5	ns	–
$\overline{\text{ADV}}$ active/inactive after BFCLKO active edge[2)]	t_{22}	CC	-2	–	2	ns	–
$\overline{\text{BAA}}$ active/inactive after BFCLKO active edge[2)]	t_{22a}	CC	-2.5	–	1.5	ns	–
Data setup to BFCLKI rising edge[3)]	t_{23}	SR	3	–	–	ns	–
Data hold from BFCLKI rising edge[3)]	t_{24}	SR	0	–	–	ns	–
$\overline{\text{WAIT}}$ setup (low or high) to BFCLKI rising edge[3)]	t_{25}	SR	3	–	–	ns	–
$\overline{\text{WAIT}}$ hold (low or high) from BFCLKI rising edge[3)]	t_{26}	SR	0	–	–	ns	–

1) An active edge can be a rising or falling edge, depending on the settings of bits BFCON.EBSE / ECSE and the clock divider ratio.
Negative minimum values for these parameters mean that the last data read during a burst may be corrupted. However, with clock feedback enabled, this value is an oversampling not required for the internal bus transaction, and will be discarded.

2) This parameter is valid for BUSCONx.EBSE = 1 and BUSAPx.EXTCLK = 00_B.
For BUSCONx.EBSE = 1 and other values of BUSAPx.EXTCLK, $\overline{\text{ADV}}$ and BAA will be delayed by 1/2 of the internal bus clock period T_{CPU} = 1 / f_{CPU}.
For BUSCONx. EBSE = 0 and BUSAPx.EXTCLK = 11_B, add 2 internal bus clock periods.
For BUSCONx. EBSE = 0 and other values of BUSAPx.EXTCLK, add 1 internal bus clock period.

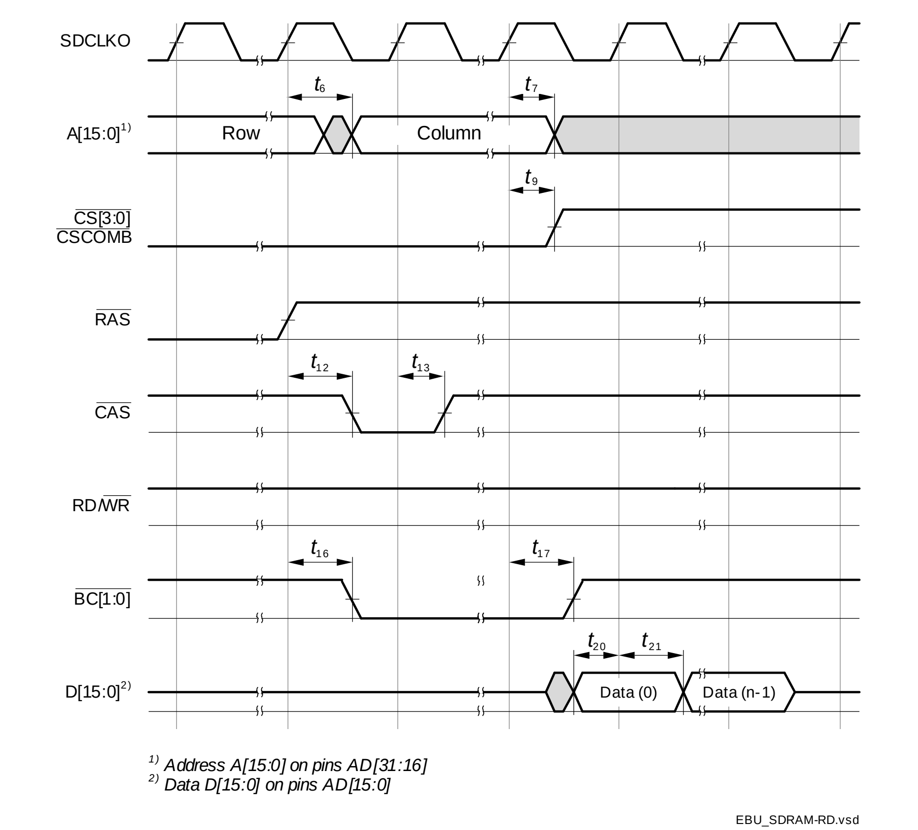

Figure 48 EBU SDRAM Read Access Timing

4.3 Quality Declarations

The qualification of the XMC4500 is executed according to the JEDEC standard JESD47H.

Note: For automotive applications refer to the Infineon automotive microcontrollers.

Table 67 Quality Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	t_{OP} CC	20	–	–	a	$T_J \leq 109°C$, device permanent on
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	–	–	2 000	V	EIA/JESD22-A114-B
ESD susceptibility according to Charged Device Model (CDM)	V_{CDM} SR	–	–	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	MSL CC	–	–	3	–	JEDEC J-STD-020D
Soldering temperature	T_{SDR} SR	–	–	260	°C	Profile according to JEDEC J-STD-020D